Technical Data
Data Sheet N2494, REV.C

RoHS

S2M0080120K
1200V SIC POWER MOSFET

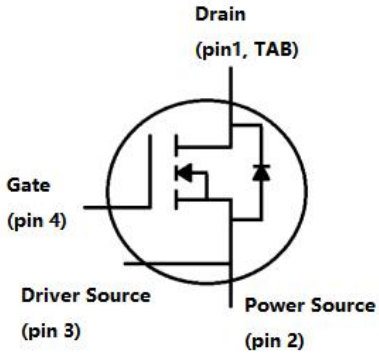
1 2 3 4

V_{DS} = 1200 V
I_{DS} = 41 A
R_{DS}(on) = 77 mΩ

Description

S2M0080120K is single SiC Power MOSFET packaged in TO-247-4 case. The device is a high voltage n-channel enhancement mode MOSFET that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S2M0080120K is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- Positive temperature characteristics, easy to parallel.
- Low on-resistance Typ. RDS(on) = 77mΩ .
- Fast switching speed and low switching losses.
- Very fast and robust intrinsic body diode.
- "-A" is an AEC-Q101 qualified device
- Process of non-bright Tin electroplatin

Applications

- EV Fast Charging Modules
- EV On Board Chargers
- Solar Inverters
- Online UPS/Industrial UPS
- SMPS (Switch Mode Power Supplies)
- DC-DC Converters
- ESS (Energy Storage Systems)

Maximum Ratings(T=25℃ unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Drain Source Voltage	V_{DSS}	V_{GS} = 0V, I_{DS} = 100uA, T_C = 25°C	1200	V
Gate Source Voltage	V_{GSS}	T_C = 25°C, Absolute maximum values, AC (f>1Hz)	-10 to +25	V
Gate Source Voltage	V_{GSOP}	T_C = 25°C Recommended Operational Values	-5 to +20	V
Continuous Drain Current	I_D	V_{GS} = 20V, T_C = 25°C	41	A
	I_D	V_{GS} = 20V, T_C = 100°C	29	A
Pulsed Drain Current	$I_{D,pulse}$	T_C=25˚C	82	A
Power Dissipation	P_D	T_C=25˚C	231	W

Technical Data
Data Sheet N2494, REV.C

RoHS

Electrical Characteristics(T=25℃ unless otherwise specified)

Characteristics	Symbol	Condition	Min.	Typ.	Max.	Units
Drain Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	1200			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 10mA	2.0	2.8	4.0	V
		V_{DS} = V_{GS}, I_D = 10mA, T_J = 175 °C		1.8		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 1200V, V_{GS} = 0V		0.1	1.0	uA
	I_{DSS}	V_{DS} = 1200V, V_{GS} = 0V, T_J = 175 °C		1		uA
Gate Source Leakage Current	I_{GSS+}	V_{GS} = 20V, V_{DS} = 0V		10	100	nA
	I_{GSS-}	V_{GS} = -5V, V_{DS} = 0V		-10	-100	nA
Drain Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 20V, I_D = 20A		77	100	mΩ
		V_{GS} = 20V, I_D = 20A, T_J = 175 °C		137		mΩ
Transconductance	gfs	V_{DS}= 20 V, I_D= 20 A		10.5		S
		V_{DS}= 20 V, I_D= 20 A, T_J = 175 °C		8		S
Input Capacitance	C_{ISS}	V_{GS} = 0V,		1324		pF
Output Capacitance	C_{OSS}	V_{DS} = 1000V		74		
Reverse Transfer Capacitance	C_{RSS}	V_{AC} = 25mV		3.4		
C_{OSS} Stored Energy	E_{OSS}	f = 200kHz		37		uJ
Turn-On Switching Energy	E_{ON}	V_{DS} = 800V, V_{GS} = -5/20V		290		uJ
Turn-Off Switching Energy	E_{OFF}	I_D = 20A, $R_{G(ext)}$= 2.5Ω		20		
Turn-On Delay Time	$t_{d(on)}$	V_{DS} = 800V, V_{GS} = -5/20V		20		ns
Rise Time	t_r	I_D = 20A, $R_{G(ext)}$= 2.5Ω, L=975uH		11		
Turn-Off Delay Time	$t_{d(off)}$	FWD=S2M0080120K		20		
Fall Time	t_f			7.8		
Internal Gate Resistance	$R_{G(int)}$	f = 1MHz, VAC = 25 mV, D-S short		3.3		Ω
Gate to Source Charge	Q_{gs}	V_{DS} = 800V, V_{GS} = -5/20V		23		nC
Gate to Drain Charge	Q_{gd}	I_D = 20A		14		
Total Gate Charge	Q_g			54		

Technical Data
Data Sheet N2494, REV.C

RoHS

Reverse Diode Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Diode Forward Voltage	V_{SD}	V_{GS}= -5V, I_{SD}= 10A	4.0		V
	V_{SD}	V_{GS}= -5V, I_{SD}= 10A, T_J= 175°C	3.5		V
Continuous Diode Forward Current	I_S	V_{GS}= -5V, T_C= 25℃		41	A
Reverse Recovery Time	t_{rr}	V_{GS}= -5V, I_{SD}= 20A, T_J= 25°C	25		ns
Reverse Recovery Charge	Q_{rr}	V_R= 800V	102		nC
Peak Reverse Recovery Current	I_{mm}	dif/dt= 1950A/μs	6.7		A

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T_{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	0.65	°C/W
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$		32	°C/W

Ordering Information:

Device	Package	Shipping
S2M0080120K	TO-247-4	30pcs/tube

Marking Diagram

Where XXXXX is YYWWL

S2M = Device Type
0080 = R_{DS}(on)
120 = Reverse Voltage (1200V)
K = Package
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ratings and Characteristics Curves

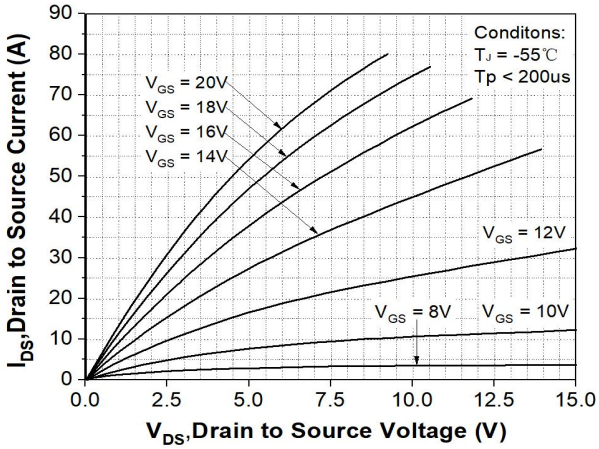


Figure 1. Output Characteristics T_J = -55 °C

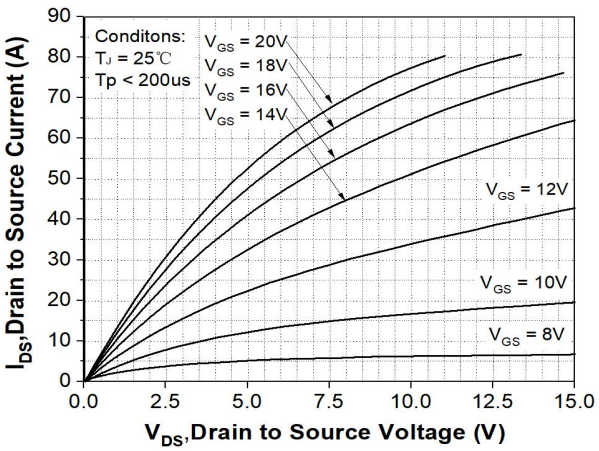


Figure 2. Output Characteristics T_J = 25 °C

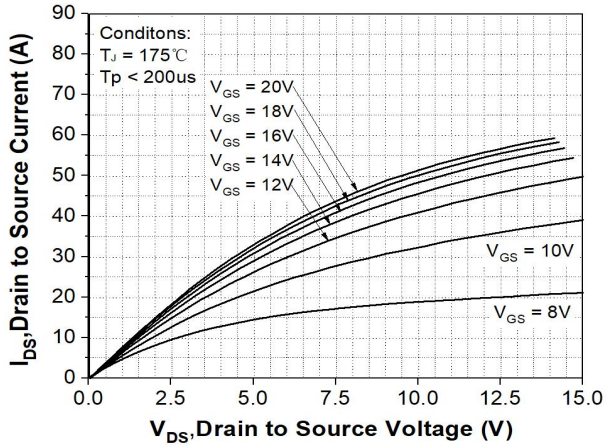


Figure 3. Output Characteristics T_J = 175°C

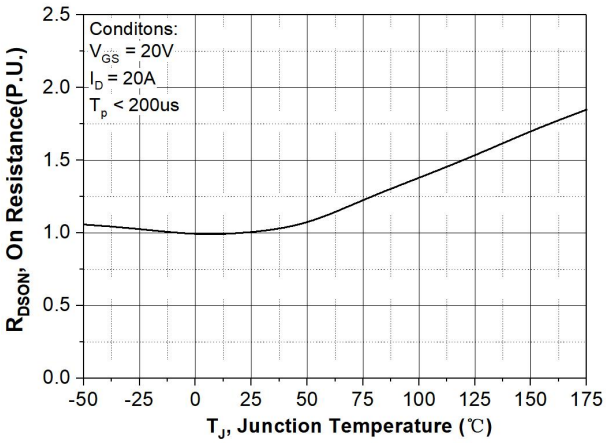


Figure 4. Normalized On-Resistance vs. Temperature

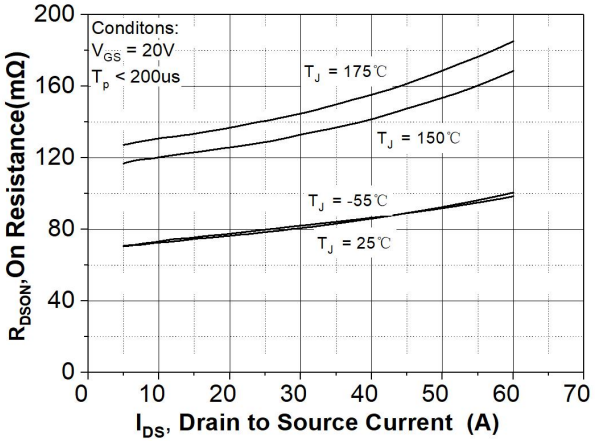


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

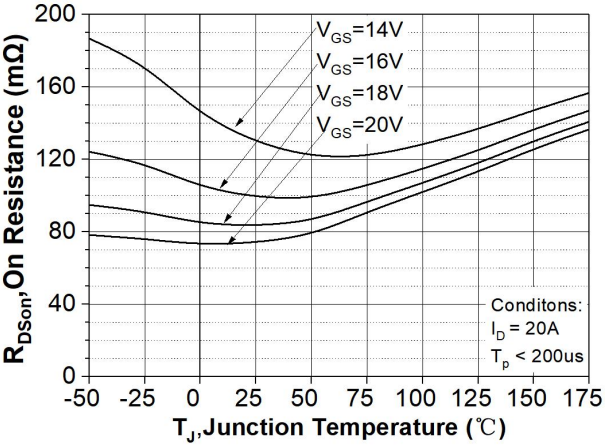


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

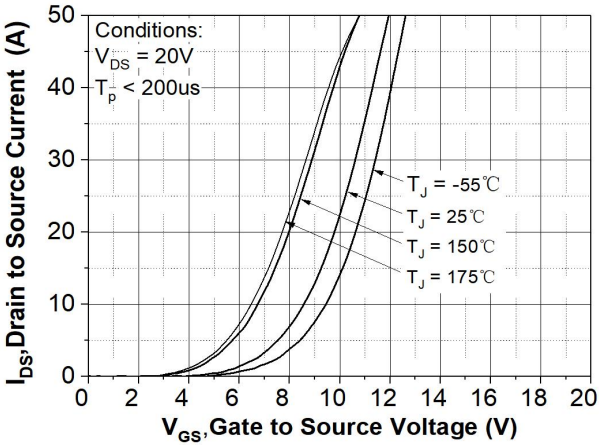


Figure 7. Transfer Characteristic for Various Junction Temperatures

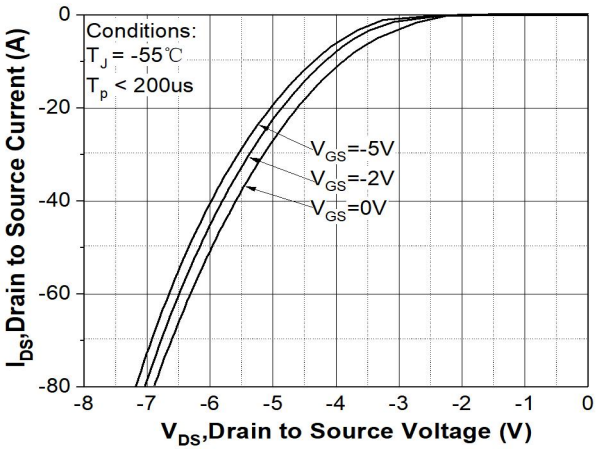


Figure 8. Body Diode Characteristic at T_J = -55 °C

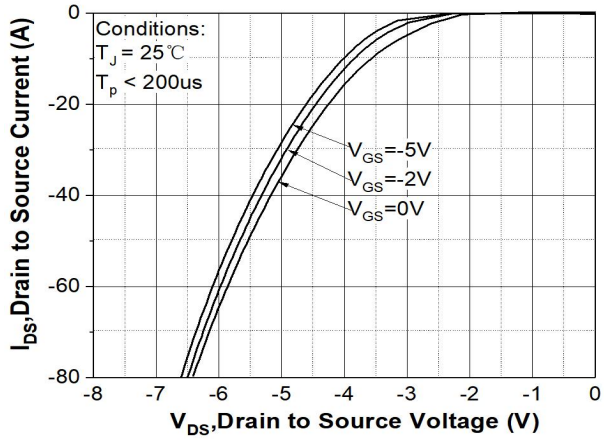


Figure 9. Body Diode Characteristic at T_J = 25 °C

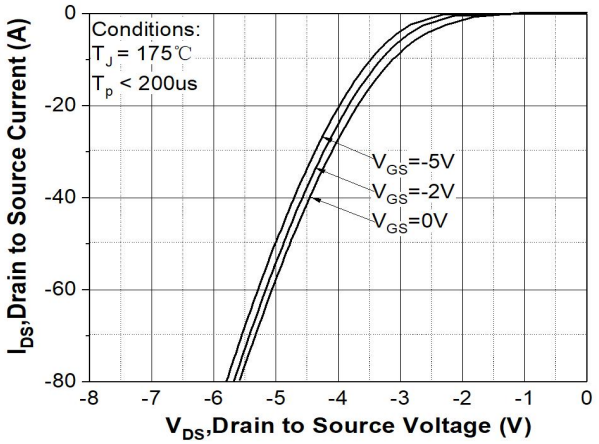


Figure 10. Body Diode Characteristic at T_J = 175 °C

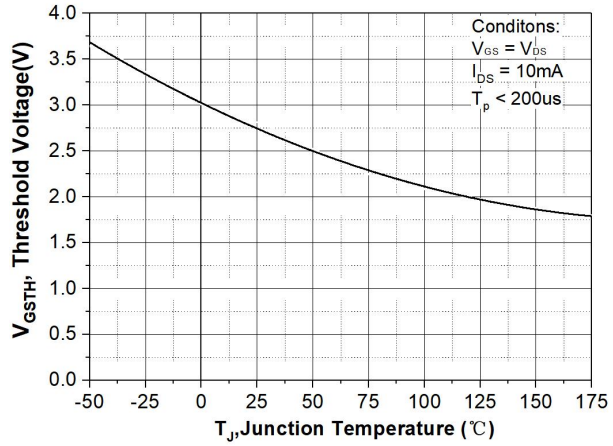


Figure 11. Threshold Voltage vs. Temperature

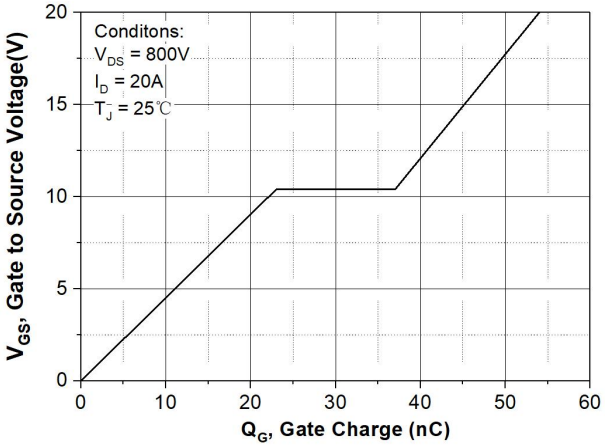


Figure 12. Gate Charge Characteristic

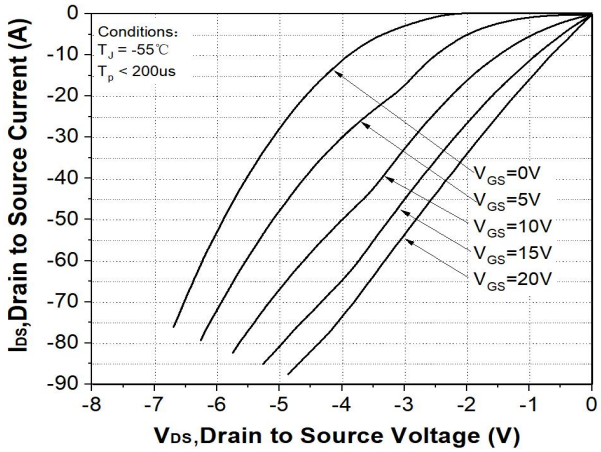


Figure 13. 3rd Quadrant Characteristic at T_J = -55 °C

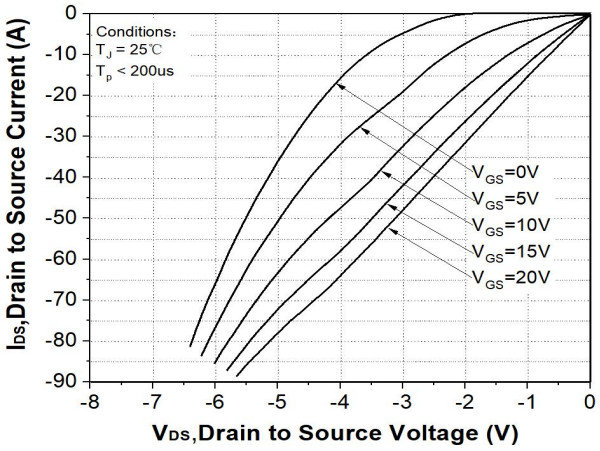


Figure 14. 3rd Quadrant Characteristic at T_J = 25 °C

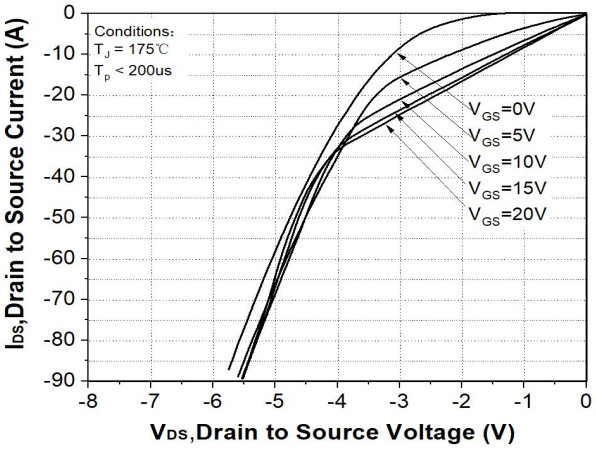


Figure 15. 3rd Quadrant Characteristic at T_J = 175°C

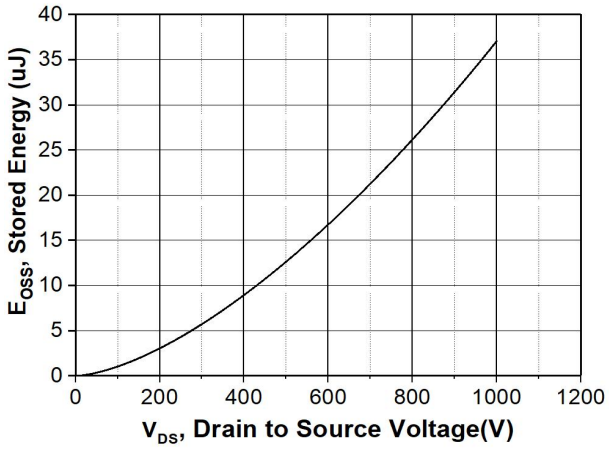


Figure 16. Output Capacitor Stored Energy

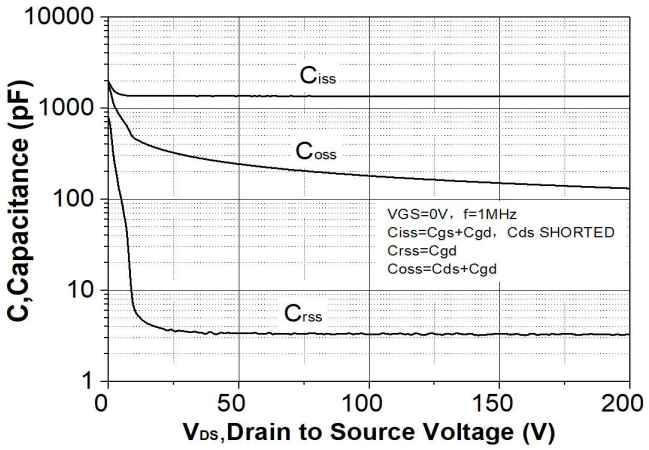


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

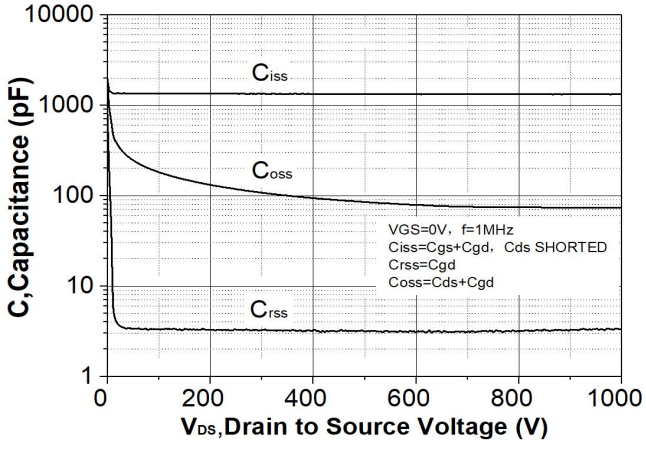


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1000V)

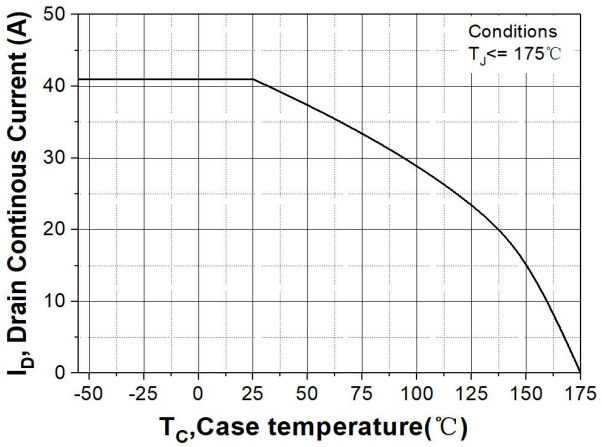


Figure 19. Continuous Drain Current Derating vs. Case Temperature

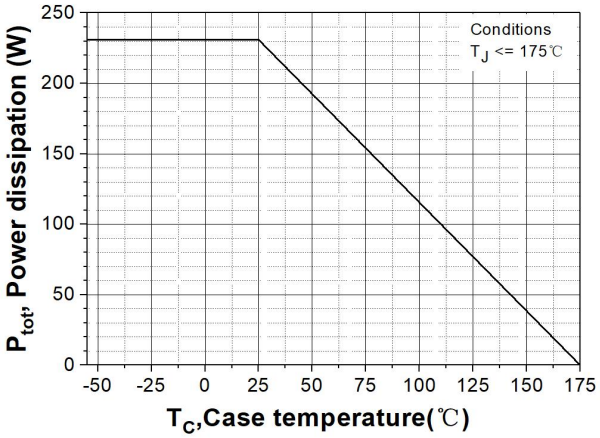


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

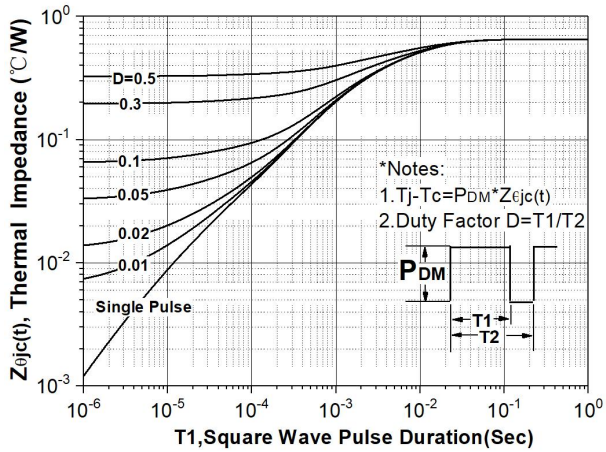


Figure 21. Transient Thermal Impedance (Junction - Case)

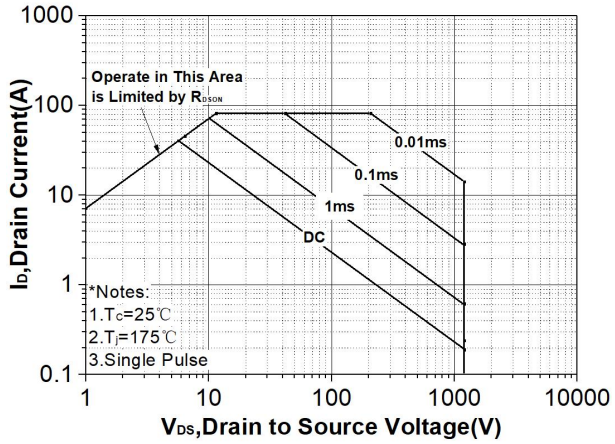


Figure 22. Safe Operating Area

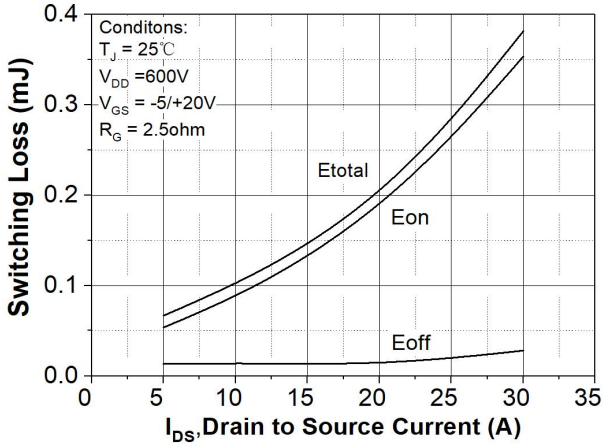


Figure 23. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 600V)

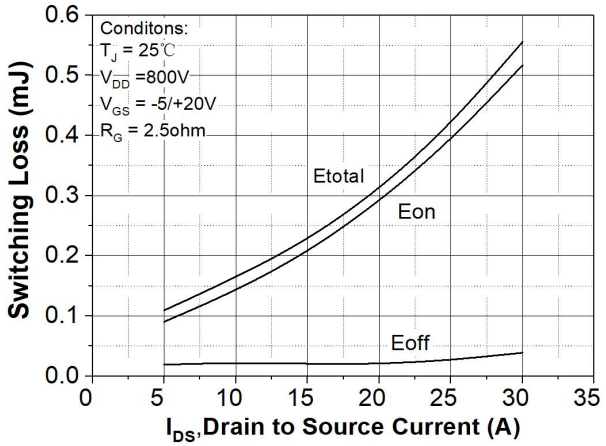


Figure 24. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 800V)

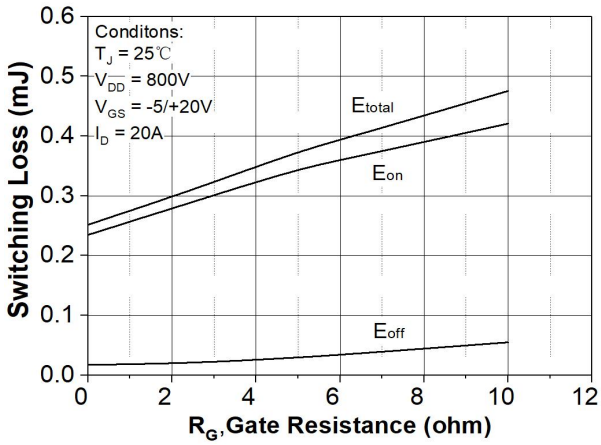


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

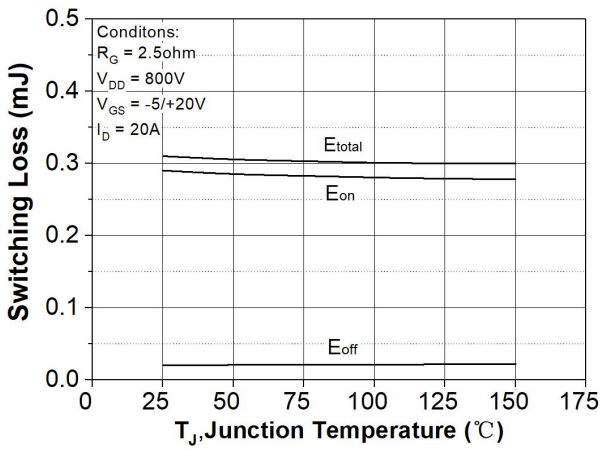


Figure 26. Clamped Inductive Switching Energy vs. Temperature

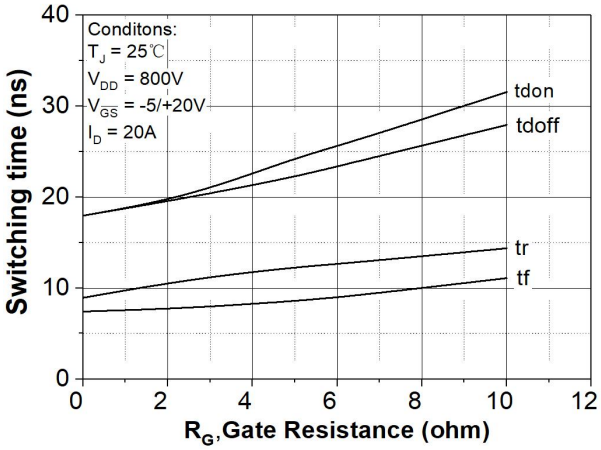


Figure 27. Switching Times vs. $R_{G(ext)}$

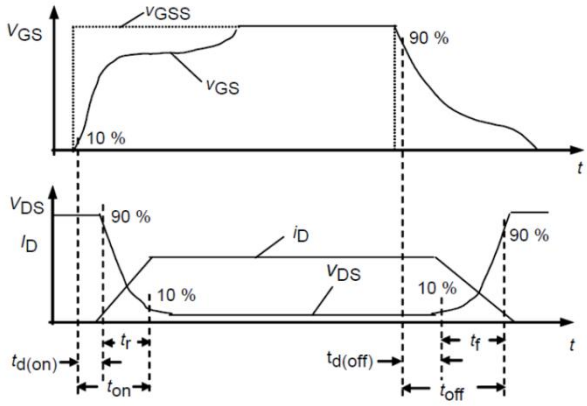
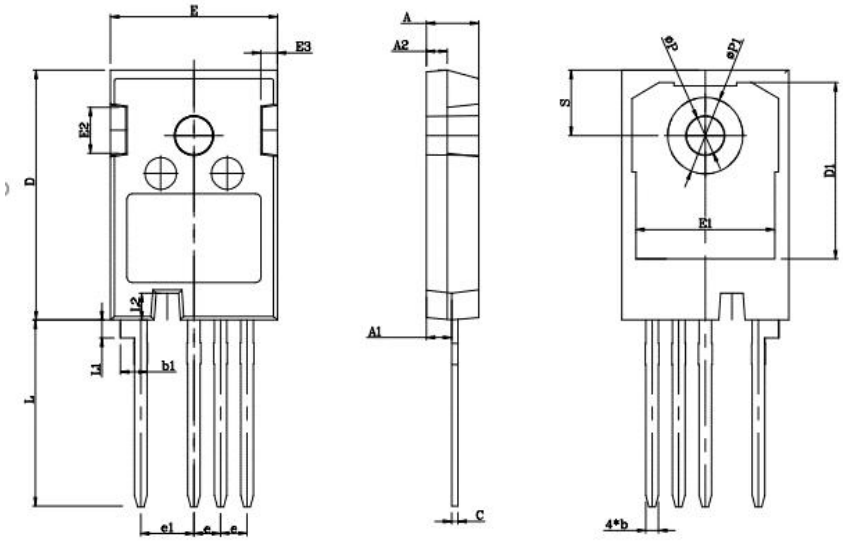


Figure 28. Switching Times Definition

Technical Data
Data Sheet N2494, REV.C

RoHS

Mechanical Dimensions TO-247-4



Symbol	In mm		
	Min	Nom	Max
A	4.80	5.00	5.21
A1	2.23	2.41	2.59
A2	1.85	2.00	2.16
b	1.07	1.20	1.36
b1	2.35	2.67	2.94
c	0.51	0.60	0.75
D	23.30	23.45	23.60
D1	16.25	16.55	17.65
E	15.75	15.94	16.13
E1	13.00	14.02	14.15
E2	3.68	4.40	5.10
E3	1.00	1.45	1.90
e	2.54 BSC		
e1	5.08 BSC		
L	17.31	17.57	17.82
L1	1.50		4.37
ΦP	3.51	3.61	3.65
ΦP1	7.19 REF		
S	6.04	6.17	6.30

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Data Sheet N2494, REV.C

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